Shottky barrier diode

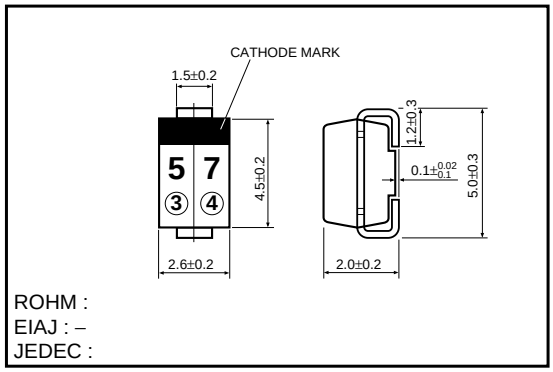
RSX501L-20

●**Application**
General rectification.

●**Features**
1) Small power mold type. (PMDS)
2) High reliability.
3) Low V_F.

●**Structure**
Silicon Epitaxial Planer

●**External dimensions** (Unit : mm)



ROHM :
EIAJ : –
JEDEC :

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Reverse voltage (repetitive peak)	V_{RM}	25	V	
Reverse voltage (DC)	V_R	20	V	
Average rectified forward current	I_O	5	A	*
Forward current surge peak (60Hz / 1cyc.)	I_{FSM}	70	A	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	–40 to 125	°C	

*On the Glass epoxy substrate, 180° Half sine wave, Tc=90°C MAX.

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.39	V	I_F=3.0A
Reverse current	I_R	–	–	500	μA	V_R=20V

●**Electrical characteristic curves** (Ta=25°C)

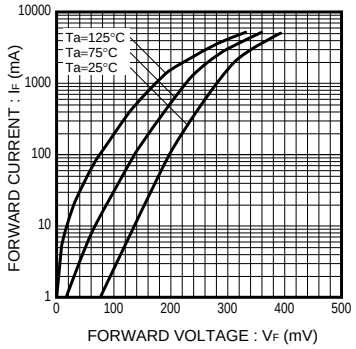


Fig.1 Forward Temperature Characteristics

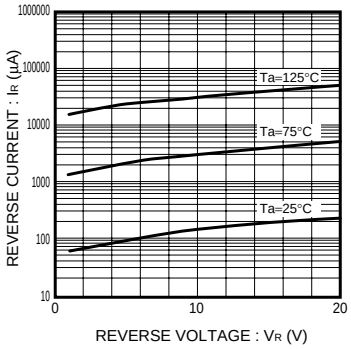


Fig.2 Reverse Temperature Characteristics

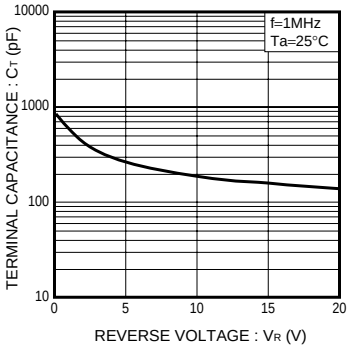


Fig.3 Capacitance Between Terminals Characteristics

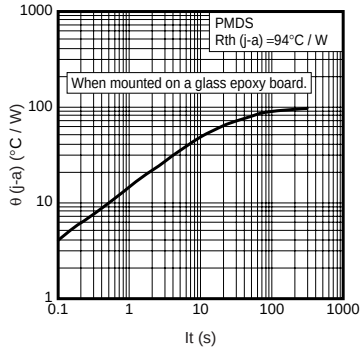


Fig.4

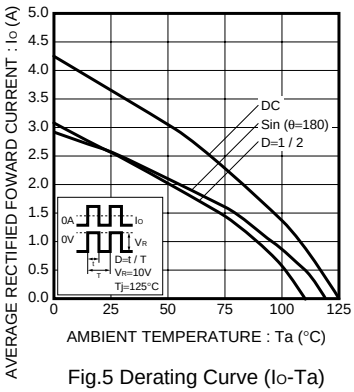


Fig.5 Derating Curve (I_O-Ta)

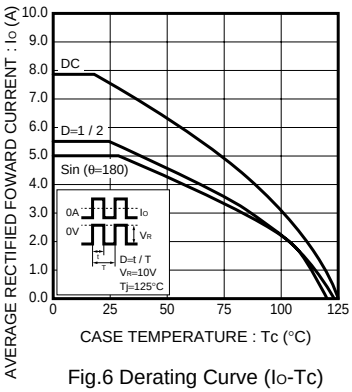


Fig.6 Derating Curve (I_O-Tc)

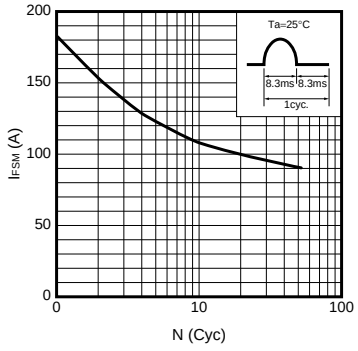


Fig.7

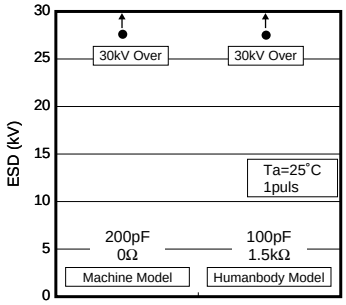


Fig.8 ESD